	Type	Hits	Search Text	DBs
1	IS&R	4	(("5384270") or ("5814859")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
2	BRS	238850	"438"/$.ccls. (MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
3	BRS	104	S2 and (silicon adj carbide adj MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
4	BRS	22	S3 and (vertical adj MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
5	BRS	239138	"438"/$.ccls. (MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

Type	Hits	Search Text	DBs
6 BRS	54	S5 and (silicon adj carbide adj MOSFET) and (ion adj implantation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
7 BRS	2	S6 and (ion adj implantation adj mask)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
8 BRS	34	S6 and range	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
9 BRS	0	S6 and (ion adj implantation adj range)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
10 BRS	239138	"438"/$.ccls. (MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

Type	Hits	Search Text	DBs
11 BRS	0	S10 and (silicon adj carbide adj MOSFET) and (implantation adj angle)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
12 BRS	104	S10 and (silicon adj carbide adj MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
13 BRS	0	S13 and (angle adj of adj implantation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
14 BRS	54	S12 and (ion adj implantation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
15 BRS	36155	"438"/$.ccls. and (angloe of implantation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

Type	Hits	Search Text	DBs
16	BRS	47516	"438"/$.ccls. and (angle of implantation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
17	BRS	0	S16 and (siliicon adj carbide adj MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
18	BRS	7447	S16 and (MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
19	BRS	475	S18 and (SiC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
20	BRS	37	S19 and (vertical adj MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB